

A mask pattern correction method includes the step of extracting a correction target edge from a design pattern, the step of calculating the distance from the correction target edge to the nearest edge of an adjacent pattern, the step of calculating the correction value by a simulation in accordance with a pattern layout present within a given range determined by the correction target edge, and moving the correction target edge on the basis of the calculated correction value when the distance calculated in the distance calculation step is smaller than a predetermined distance, and the step of moving the correction target edge on the basis of an correction value set as a rule in advance in accordance with the distance when the distance calculated in the distance calculation step is larger than the predetermined distance.